PRELIMINARY DATA SHEET



BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC2731GS$

L-BNAD SILICON DOWNCONVERTER IC WITH AGC AMPLIFIER FOR DBS TUNER AND MOBILE COMMUNICATIONS

DESCRIPTION

 μ PC2731GS is a silicon monolithic integrated circuit designed for DBS tuner and mobile communications. This IC consists of double balanced mixer, local oscillator, IF amplifier, regulator and AGC amplifier. This means that L-band downconverter and AGC amplifier are integrated in 1 chip. This 1 chip IC is packaged in 20 pin SOP suitable for high-density surface mounting. Thus, this product contributes to produce physically-small DBS tuner and mobile communication equipments.

The μ PC27×× series is manufactured using NEC's 20 GHz ft NESATTM III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion and migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

- L-Band Operation fRF = 0.9 G to 2.0 GHz
- · L-Band downconverter and AGC amplifier are integrated in 1 chip.
- · Internal double balanced mixer minimizes carrier leak.
- 50 Ω impedance output.
- · Supply voltage 5.0 V TYP.
- Circuit current Icctotal = 69 mA (Downconverter: 42 mA, AGC Amplifier: 27 mA)
- · Packaged in 20 pin SOP suitable for high-density surface mounting.

ORDERING INFORMATION

PART NUMBER	PACKAGE	SUPPLYING FORM
μPC2731GS-E1	20 pin plastic SOP (300 mil)	Embossed tape 24 mm wide. Pin 1 indicates pull-out direction of tape. QTY 2.5 kp/REEL.
μPC2731GS-E2	20 pin plastic SOP (300 mil)	Embossed tape 24 mm wide. Pin 1 indicates roll-in direction of tape. QTY 2.5 kp/REEL.

^{*} For evaluation sample order, please contact your local NEC sales office (Part number: μPC2731GS).

Caution: Electro-static sensitive device

The information in this document is subject to change without notice.

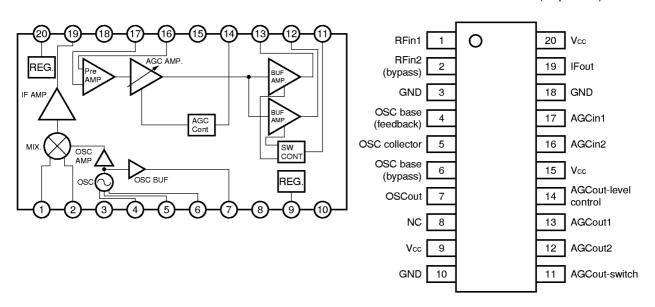
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INTERNAL BLOCK DIAGRAM

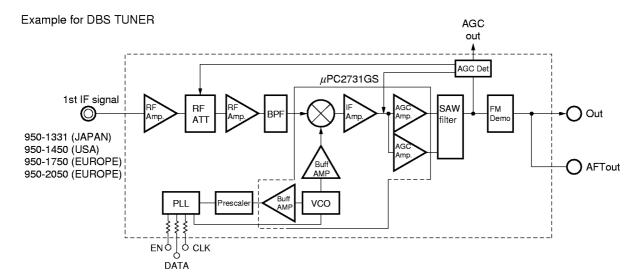
PIN CONNECTIONS (Top View)



SELECTOR GUIDE (TA = +25 °C, Vcc = 5.0 V)

Main Feature	Device Number	f _{RF} (GHz)	CG (dB)	NF (dB)	D _{AGC} (dB)	Gago max. (dB)	Package
50 $Ω$ impedance output	μPC2721GR	0.9 - 2.0	21	11	-	_	8 pin SOP
High impedance output	μPC2722GR	0.9 - 2.0	18	11	_	_	8 pin SOP
Equipped with AGC amplifier 50 Ω impedance output	μPC2731GS	0.9 - 2.0	14	14	60	25	20 pin SOP

TYPICAL SYSTEM APPLICATION



To know the detail in associated products, please refer to their latest data sheet.



PIN EXPLANATIONS

Pin No.	Symbol	Pin Voltage (V)	Explanation	Equivalent Circuit
1	RF input 1	2.4	① and② pins are inputs for mixer designed as double balanced type. Either pin can be assigned for input and another for ground.	
2	RF input 2 (bypass)	2.4		
3	GND	0*	Must be connected to the system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. (Track length should be kept as short as possible.)	
4	OSC base (feedback)	2.9	Internal oscillator consist in balance amplifier. (4) and (5) pins should be externally equipped with tank resonater circuit in or-der to oscillate with feedback loop.	4 (5) (6) Vcc +
5	OSC collector	5.0	pin should be grounded through coupling capacitor (e.g. 0.5 pF).	
6	OSC base (bypass)	2.9	(5) pin is defined as open collector. This pin should be coupled through resistor or chock coil in order to adjust Q and be supplied voltage to. In case of undesired oscillation, adjust its Q lower to stabilize the operation.	Vcc Vcc
7	OSC OUTPUT	3.7	Oscillator output pin. Must be connected PLL synthesizer IC's input pin.	osc → -[
8	NC	-	Non connection pin.	
9	Vcc	5.0 ± 0.5*	AGC amplifier's power supply pin. Operates on 5.0 ± 0.5 V bias supply. Must be connected bypass capacitor (e.g. 1 000 pF) to minimize ground impedance.	
10	GND	0*	Must be connected to the system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. (Track length should be kept as short as possible).	

^{*} Externally supply voltage



Pin No.	Symbol	Pin Voltage (V)	Explanation	Equivalent Circuit
11	AGC out switch (SW control)	Vsw* H: 5 V L: 0 V	and (3) pins are outputs of AGC amplifier. These pins can be selected by Vsw voltage to (11) pin. AGC out pin out Pin No.	11 W V C C
12	AGCo∪т₂	2.2	H: 5 V out 1 1 13	Vcc Vcc
13	AGCout1	2.2	Vsw L: Open out 2 ② or GND Both ① and ① output with 50 Ω impedance constant.	13
14	AGC out level control	(open: 2.0) 0 to 5.0*	Auto gain control pin. This pin's bias govern the AGC out level.	Vcc GND
15	Vcc	5.0 ± 0.5*	Supply voltage pin for AGC amplifier. Must be conneced bypass capacitor (e.g. 1 000 pF) to minimize ground impedance.	
16	AGC in 2 (bypass)	2.0	Bypass pin of AGC amplifier input. Must be grounded through capacitor.	Vcc
17	AGC in 1	2.0	Input of AGC amplifier. Must be coupled with capacitor to cut DC. (e.g. 1 000 pF)	
18	GND	0*	Ground pin of AGC amplifier. Must be connected to the system ground with minimum inductance. Ground pattern should be formed as wide as possible. (Track length be kept as short as possible.)	
19	IFоuт	2.0	Output from IF amplifier of downconverter. This amplifier is designed as single-end push-pull amplifier. This pin is assigned for the emitter follower output whit 50 Ω impedance.	Vcc 19
20	Vcc	5.0 ± 0.5*	Downconverter's power supply pin. Operates on 5.0 ± 0.5 V. Must be connected bypass capacitor (e.g. 1 000 pF) to minimize ground impedance.	

^{*} Externally supply voltage



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	Vcc	TA = + 25 °C	6.0	V
AGC control voltage	V_{AGC}	T _A = + 25 °C	5.5	٧
SW control voltage	V_{SW}	TA = + 25 °C	5.5	٧
Power dissipation depend on package	P □	Mounted on $50 \times 50 \times 1.6$ mm double copper clad epoxy glass board at T _A = + 85 °C	640	mW
Operating temperature	T_{opt}		-20 to +85	۰C
Storage temperature	Tstg		-65 to +150	°C

RECOMMENDED OPERATING RANGE

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	Vcc	4.5	5.0	5.5	٧
AGC control voltage	Vage	0	1	5.0	٧
SW control voltage	Vsw	0	-	5.0	٧
Operating temperature	Topt	-20	+25	+85	°C

ELECTRICAL CHARACTERISTICS (Ta = + 25 °C, Vcc = 5.0 V, ZL = Zs = 50 Ω)

PARAMETERS		SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
	Downconverter	lcc	28.7	42.0	54.0	mA	No Input Signal
Circuit current	AGC Amplifier		13.3	27	38		
	IC Total		44	69	92		
DOWNCONVERT	ER BLOCK: UNLES	SS OTHERWI	SE SPEC	IFIED, fiFou	t = 403 MH	Нz	
Lower RF input fre	equency	faFi			0.9	GHz	Pin = - 30 dBm
Upper RF input fre	equency	fRFu	2.0			GHz	P _{in} = - 30 dBm
Conversion gain 1		CG1	11.5	14.5	17.5	dB	fr= 900 MHz
Conversion gain 2	!	CG2	10.5	13.5	16.5	dB	frr = 2 GHz
IF maximum outp	ut	Posat	0	+7	+10	dBm	frr = 2 GHz
Noise figure 1		NF1		12	15	dB	fr= 900 MHz
Noise figure 2		NF2		17	20	dB	frr = 2 GHz
AGC AMPLIFIER	BLOCK: UNLESS C	THERWISE	SPECIFIE	D, fiFin = 40	03 MHz		
Lower AGC input	frequency	fıFı			140	MHz	3 dB down CG from fı⊧ın = 403 MHz
Upper AGC input	frequency	fıFu	550			MHz	3 dB down CG from firin = 403 MHz
Conversion gain 1		G _Р МАХ.		25		dB	P _{in} = −60 dBm
Conversion gain 2	2	G _{РМІN.}		-40		dB	P _{in} = −10 dBm
Gain Control Ranç	ge	GC	45	65		dB	V _{AGC} = 0 to 5.0 V, P _{in} = -30 dBm

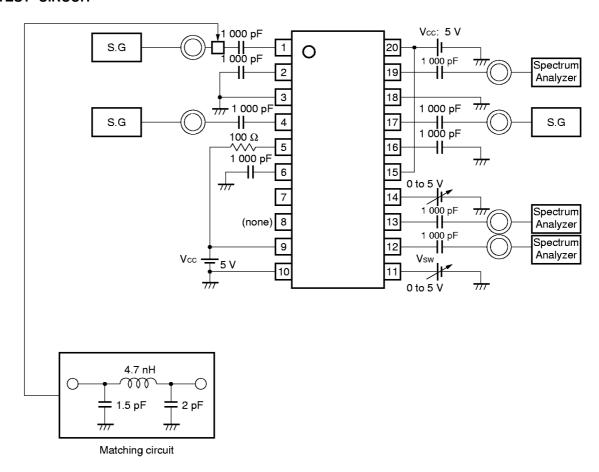


STANDARD CHARACTERISTIC FOR REFERENCE (Ta = +25 °C, Vcc = 5.0 V, ZL = Zs = 50 Ω)

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION	
DOWNCONVERTER BLOCK: UNLESS OTHERWISE SPECIFIED, firout = 403 MHz							
3rd order intermodulation distortion	IМз		-39		dBc	f _{RF} = 2.0 GHz, 2.04 GHz P _{in} = - 30 dBm	
Local oscillator frequency	Local	1.3		2.4	GHz	Internal local oscillating	
Noise figure 2'	NF2'		14		dB	Internal local oscillating fRF = 2 GHz	
AGC AMPLIFIER BLOCK: UNLESS C	THERWISE	SPECIFIE	D, fiFin = 40	03 MHz			
Input dynamic range	Drange		60		dBc	Range kept Po = −30 ± 1 dB	
3rd order intermodulation distortion	IМз		-50		dBc	f _{IFin} = 400 MHz, 420 MHz V _{AGC} = 0 V, Po = -20 dBm	
SW control voltage	Vsw	4	5	6	٧	AGCout1	
		0	0	1	V	AGCout2	



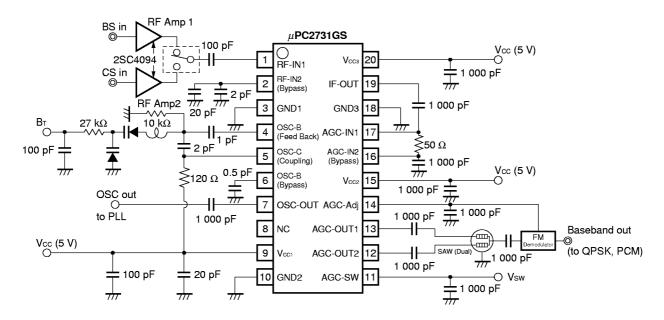
TEST CIRCUIT



	/	AGC out pin			
		Output	Pin No.		
	H: 5 V	output 1	13		
V _{sw} 11 pin	L: Open or 0 V	output 2	12		



APPLICATION CIRCUIT EXAMPLE

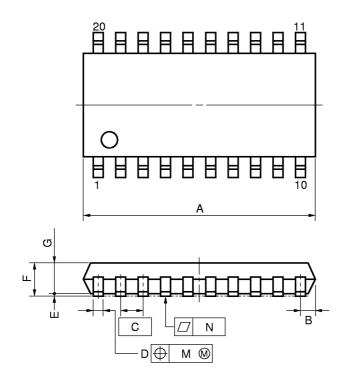


The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

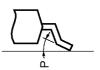


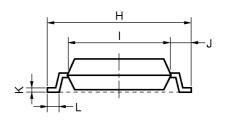
PACKAGE DIMENSIONS

20 PIN PLASTIC SOP (300 mil)



detail of lead end





NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	13.00 MAX.	0.512 MAX.
В	0.78 MAX.	0.031 MAX.
С	1.27 (T.P.)	0.050 (T.P.)
D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$
E	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55	0.061
Н	7.7± 0.3	0.303±0.012
1	5.6	0.220
J	1.1	0.043
K	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
М	0.12	0.005
N	0.10	0.004
Р	3° ⁺⁷ °	3°+7°

P20GM-50-300B, C-4



NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electrostatic sensitive devices.
- (2) Form a ground pattern as wide as possible to prevent increase in ground impedance (which can cause undesired oscillation).
- (3) Keep the track length of the ground pins as short as possible.
- (4) Connect a bypass capacitor (having, for example, a capacitance of 1 000 pF) to the Vcc pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered in the following recommended conditions. Other soldering method and conditions than the recommended conditions are to be consulted with out sales representatives.

μ PC2731GS

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak package's surface temperature: 230 °C or below, Reflow time: 30 seconds or below (210 °C or higher), Number of reflow process: 1, Exposure limit*: None	IR30-00-1
VPS	Peak package's surface temperature: 215 °C or below, Reflow time: 40 seconds or below (200 °C or higher), Number of reflow process: 1, Exposure limit*: None	VP15-00-1
Wave soldering	Solder temperature: 260 °C or below, Flow time: 10 seconds or below, Number of flow process: 1, Exposure limit*: None	WS60-00-1
Partial heating method	Terminal temperature: 300 °C or below, Flow time: 3 seconds or below, Exposure limit*: None	

^{*} Exposure limit before soldering after dry-pack package is opened.

Storage conditions: 25 °C and relative humidity at 65 % or less.

Note Apply only a single process at once, except for "Partial heating method".

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E)